



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

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37 C.F.R. 1.8

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PRELIMINARY AMENDMENT

IN THE SPECIFICATION:

1. When contact is made between an n-type semiconductor and a conductor whose work function Φ_m is less than half of $(E_g/2 - \chi)$ where E_g is the semiconductor band gap and χ is the electron affinity, then charge exchange occurs to obtain equilibrium;

3. the greater the positive difference between $(E_g/2 + \chi - \Phi_m)$ and work function Φ_m the greater charge exchange occurs to achieve equilibrium, filling some bulk traps as well; and.”.

REMARKS

The above amendments are made to correct some typographical errors in the specification. No new matter is added. Early and favorable action in connection with this application is respectfully requested.

Respectfully submitted,



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APPENDIX

IN THE SPECIFICATION:

1. When contact is made between an n-type semiconductor and a conductor whose work function Φ_m is less than half of $[(E_g/2 - \chi)]$ $(E_g/2 - \chi)$ where E_g is the semiconductor band gap and χ is the electron affinity, then charge exchange occurs to obtain equilibrium;

3. the greater the positive difference between $[(E_g/2 - \Phi_m)]$ $(E_g/2 + \chi - \Phi_m)$ and work function Φ_m the greater charge exchange occurs to achieve equilibrium, filling some bulk traps as well; and.”.